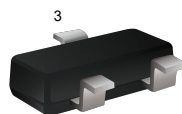
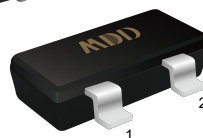


SOT-23

$V_{(BR)DSS}$	$R_{DS(on)Typ}$	$I_D Max$
60V	79mΩ@10V	3A
	90mΩ@4.5V	



1. Gate
2. Source
3. Drain



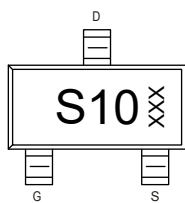
Features

- High power and current handing capability
- Lead free product is acquired
- Surface mount package

Application

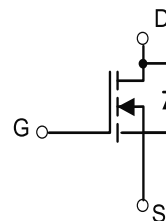
- Battery Switch
- DC/DC Converter

Marking



XXX:Date Code

Equivalent Circuit



Absolute Maximum Ratings ($T_A=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current	I_D	3	A
Pulsed Drain Current (Note 1)	I_{DM}	10	A
Power Dissipation(Note 2)	P_D	0.35	W
Thermal Resistance from Junction to Ambient(Note 2)	$R_{\theta JA}$	357	$^{\circ}C/W$
Junction Temperature and Storage Temperature	T_J, T_{stg}	-50 ~150	$^{\circ}C$

Notes: Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Ta = 25°C unless otherwise specified

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V_{(BR)DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250μA	60	--	--	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=60V, V_{GS}=0V	--	--	1	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V, V_{DS}=0V	--	--	±100	nA
V_{GS(TH)}	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250μA	0.5	--	2	V
R_{DS(ON)}	Drain-Source On-State Resistance(Note 3)	V_{GS}=10V, I_D=3A	--	79	105	mΩ
		V_{GS}=4.5V, I_D=2A	--	90	125	mΩ

Dynamic Electrical Characteristics

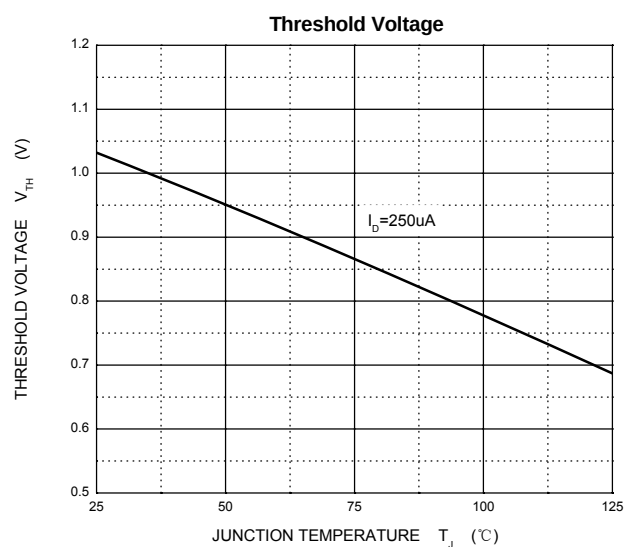
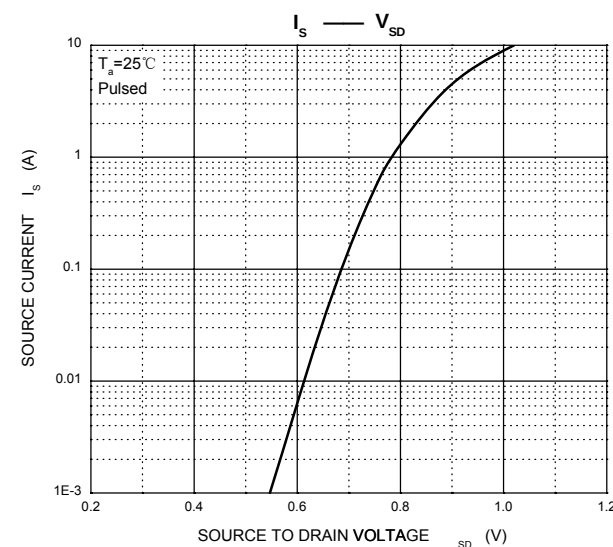
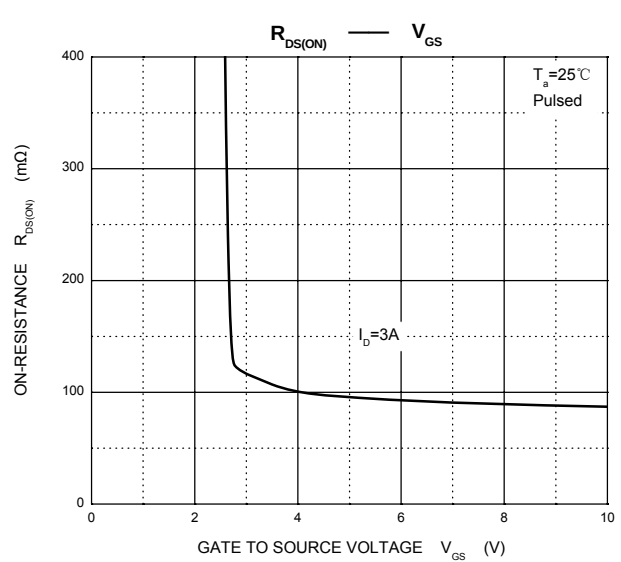
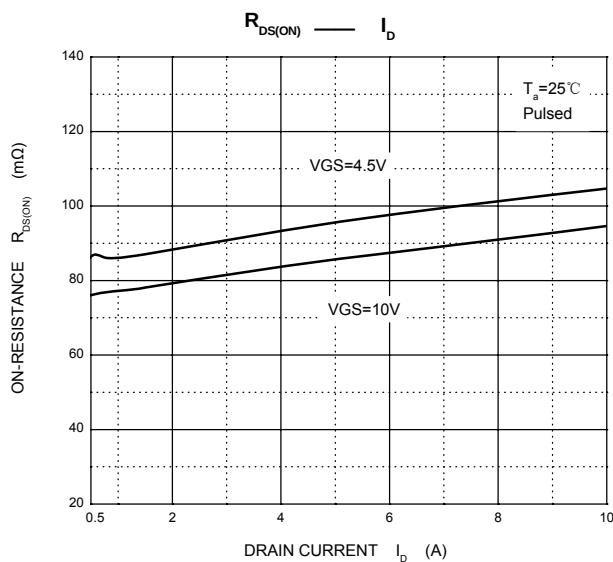
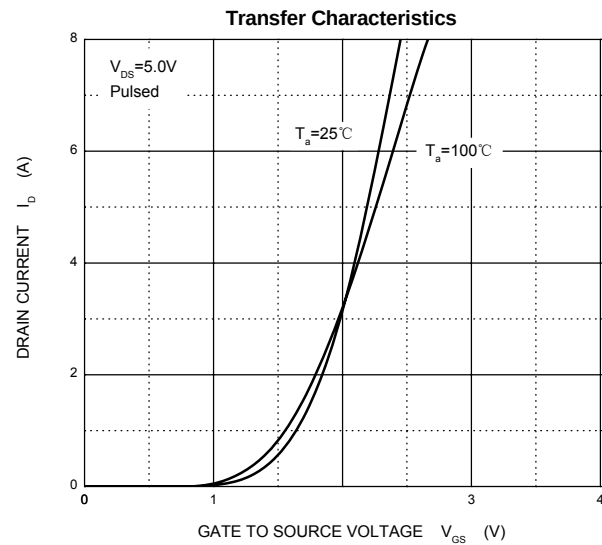
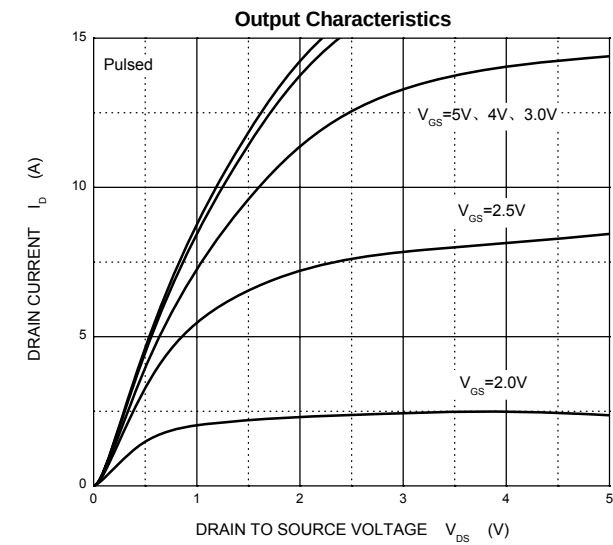
Symbol	Parameter	Condition	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	V_{DS}=30V V_{GS}=0V f=1MHz	--	247	--	pF
C_{oss}	Output Capacitance		--	34	--	pF
C_{rss}	Reverse Transfer Capacitance		--	19.5	--	pF
Q_g	Total Gate Charge	V_{DS}=30V V_{GS}=4.5V I_D=3A	--	6	--	nC
Q_{gs}	Gate Source Charge		--	1	--	nC
Q_{gd}	Gate Drain Charge		--	1.3	--	nC

Switching Characteristics

Symbol	Parameter	Condition	Min	Typ	Max	Unit
t_{d(on)}	Turn on Delay Time	V_{DS}=30V V_{GS} =10V I_D=1.5A R_G=1Ω	--	6	--	ns
t_r	Turn on Rise Time		--	15	--	ns
t_{d(off)}	Turn Off Delay Time		--	15	--	ns
t_f	Turn Off Fall Time		--	10	--	ns

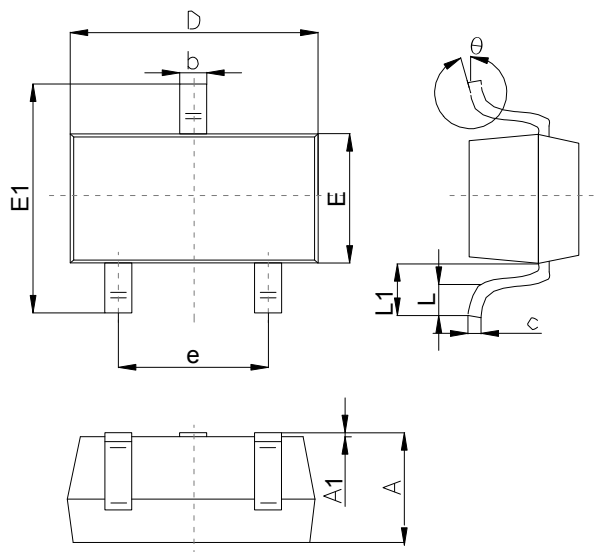
- Notes:**
- 1.Pulse width limited by maximum allowable junction temperature
 - 2.The value of P_D&R_{θJA} is measured with the device mounted on 1 in² FR-4 board with 2oz.Copper, double sided, in a still air environment with Ta=25°C.
 - 3.Pulse test ; Pulse width≤300us, duty cycle≤2%

Typical Characteristics



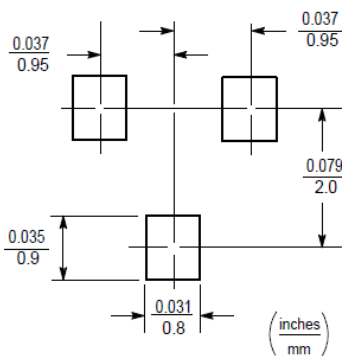
Outlitne Drawing

SOT-23 Package Outline Dimensions



Symbol	Dimensions In Millimeters		
	Min	Typ	Max
A	0.65		1.40
A1	0.00		0.20
b	0.30		0.55
c	0.08		0.20
D	2.70		3.10
E	1.15		1.65
E1	2.10		2.80
e	1.70		2.10
L	0.15		0.50
L1	0.35		0.70
θ	0°		12°

Suggested Pad Layout



- Note:
- 1. Controlling dimension: in/millimeters.
 - 2. General tolerance: $\pm 0.05\text{mm}$.
 - 3. The pad layout is for reference purposes only.